L Number	Hits	Search Text	DB	Time stamp
1	530	((multi$1layer$3 multiple$1layer$3 double$1layer$3 two$1layer$3 triple$1layer$2)near7(source and drain))	USPAT; US-PGPUB	2003/12/30 20:55
2	296	(((multi$1layer$3 multiple$1layer$3 double$1layer$3 two$1layer$3 triple$1layer$2)near7(source and drain))) and(thin adj film adj transistor$2 tft lcd soi display$2 silicon adj insulator$2)	USPAT; US-PGPUB	2003/12/30 20:55
3	238	((contact via through) adj3(hole$2)) and (((((multi$1layer$3 multiple$1layer$3 double$1layer$3 two$1layer$3 triple$1layer$2)near7(source and drain))) and(thin adj film adj transistor$2 tft lcd soi display$2 silicon adj insulator$2))	USPAT; US-PGPUB	2003/12/30 21:02
4	172	((molybdenum MO chrom$4 cr tantalum ta tungsten titanium)near21(aluminum))and (((contact via through) adj3(hole$2)) and ((((((multi$1layer$3 multiple$1layer$3 double$1layer$3 two$1layer$3 triple$1layer$2)near7(source and drain))) and(thin adj film adj transistor$2 tft lcd soi display$2 silicon adj insulator$2)))	USPAT; US-PGPUB	2003/12/30 21:00
5	187	((multi$1layer$3 multiple$1layer$3 double$1layer$3 two$1layer$3 triple$1layer$2)near7(source and drain))	EPO; JPO; DERWENT	2003/12/30 20:55
6	51	(((multi$1layer$3 multiple$1layer$3 double$1layer$3 two$1layer$3 triple$1layer$2)near7(source and drain))) and(thin adj film adj transistor$2 tft lcd soi display$2 silicon adj insulator$2)	EPO; JPO; DERWENT	2003/12/30 20:56
7	7	((contact via through) adj3(hole$2)) and (((((multi$1layer$3 multiple$1layer$3 double$1layer$3 two$1layer$3 triple$1layer$2)near7(source and drain))) and(thin adj film adj transistor$2 tft lcd soi display$2 silicon adj insulator$2))	EPO; JPO; DERWENT	2003/12/30 20:56
8	2	((molybdenum MO chrom$4 cr tantalum ta tungsten titanium)near21(aluminum))and (((((multi$1layer$3 multiple$1layer$3 double$1layer$3 two$1layer$3 triple$1layer$2)near7(source and drain))) and(thin adj film adj transistor$2 tft lcd soi display$2 silicon adj insulator$2))	EPO; JPO; DERWENT	2003/12/30 21:00
9	169	(steep step$2 deep)and (((molybdenum MO chrom$4 cr tantalum ta tungsten titanium)near21(aluminum))and (((contact via through) adj3(hole$2)) and ((((multi$1layer$3 multiple$1layer$3 double$1layer$3 two$1layer$3 triple$1layer$2)near7(source and drain))) and(thin adj film adj transistor$2 tft lcd soi display$2 silicon adj insulator$2))))	USPAT; US-PGPUB	2003/12/30 21:08
10	8	(deep)and (((molybdenum MO chrom$4 cr tantalum ta tungsten titanium)near21(aluminum))and (((contact via through) adj3(hole$2)) and ((((multi$1layer$3 multiple$1layer$3 double$1layer$3 two$1layer$3 triple$1layer$2)near7(source and drain))) and(thin adj film adj transistor$2 tft lcd soi display$2 silicon adj insulator$2))))	USPAT; US-PGPUB	2003/12/30 21:01
11	22	(((contact via through) adj3(hole$2))near31(steep step$2 deep)) and ((((multi$1layer$3 multiple$1layer$3 double$1layer$3 two$1layer$3 triple$1layer$2)near7(source and drain))) and(thin adj film adj transistor$2 tft lcd soi display$2 silicon adj insulator$2))	USPAT; US-PGPUB	2003/12/30 21:02
12	9	(steep)and (((molybdenum MO chrom$4 cr tantalum ta tungsten titanium)near21(aluminum))and (((contact via through) adj3(hole$2)) and ((((multi$1layer$3 multiple$1layer$3 double$1layer$3 two$1layer$3 triple$1layer$2)near7(source and drain))) and(thin adj film adj transistor$2 tft lcd soi display$2 silicon adj insulator$2))))	USPAT; US-PGPUB	2003/12/30 21:09